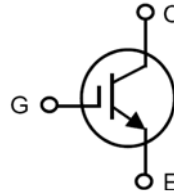


# XPT™ 600V IGBT GenX3™

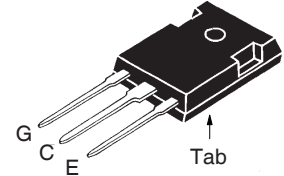
## IXXH30N60B3

Extreme Light Punch Through  
IGBT for 5-30 kHz Switching



$V_{CES} = 600V$   
 $I_{C110} = 30A$   
 $V_{CE(sat)} \leq 1.85V$   
 $t_{fi(typ)} = 125ns$

### TO-247 AD



G = Gate      C = Collector  
 E = Emitter    Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	60	A
$I_{C110}$	$T_C = 110^\circ C$	30	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	115	A
$I_A$	$T_C = 25^\circ C$	20	A
$E_{AS}$	$T_C = 25^\circ C$	250	mJ
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 48$ @ $V_{CE} \leq V_{CES}$	A
<b>t<sub>sc</sub></b> <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 360V$ , $T_J = 150^\circ C$ $R_G = 82\Omega$ , Non Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	270	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in
<b>Weight</b>		6	g

### Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Avalanche Capability
- Short Circuit Capability
- International Standard Package

### Advantages

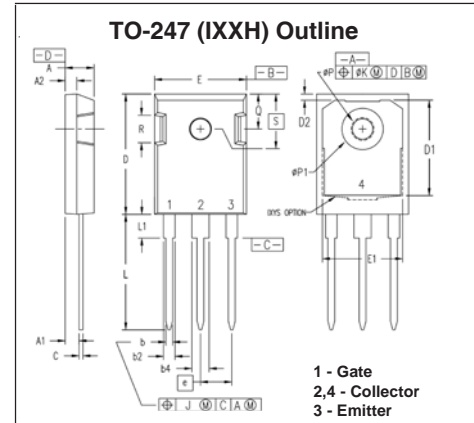
- High Power Density
- 175 $^\circ C$  Rated
- Extremely Rugged
- Low Gate Drive Requirement

### Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			25 $\mu A$ 250 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 24A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		1.66 1.97	V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 24\text{A}, V_{CE} = 10\text{V}$ , Note 1	8	14	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1185	pF
$C_{oes}$			137	pF
$C_{res}$			25	pF
$Q_{g(on)}$	$I_C = 24\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		39	nC
$Q_{ge}$			9	nC
$Q_{gc}$			17	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 24\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		23	ns
$t_{ri}$			36	ns
$E_{on}$			0.55	mJ
$t_{d(off)}$			97	150 ns
$t_{fi}$			125	ns
$E_{off}$			0.50	0.80 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 24\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		23	ns
$t_{ri}$			34	ns
$E_{on}$			1.10	mJ
$t_{d(off)}$			112	ns
$t_{fi}$			180	ns
$E_{off}$			0.70	mJ
$R_{thJC}$			0.55	$^\circ\text{C/W}$
$R_{thCS}$		0.21		$^\circ\text{C/W}$



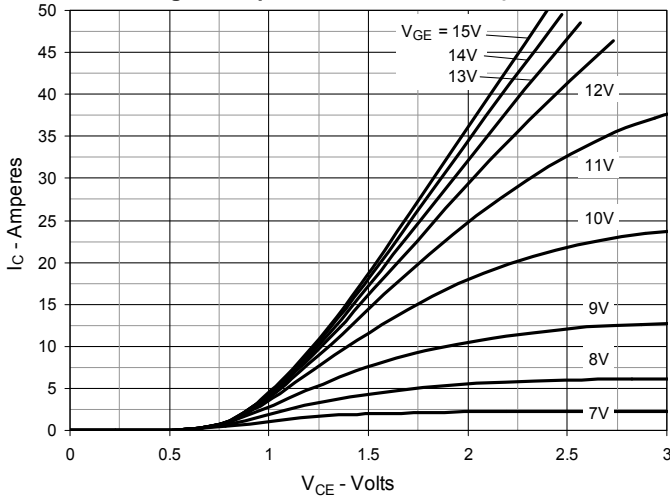
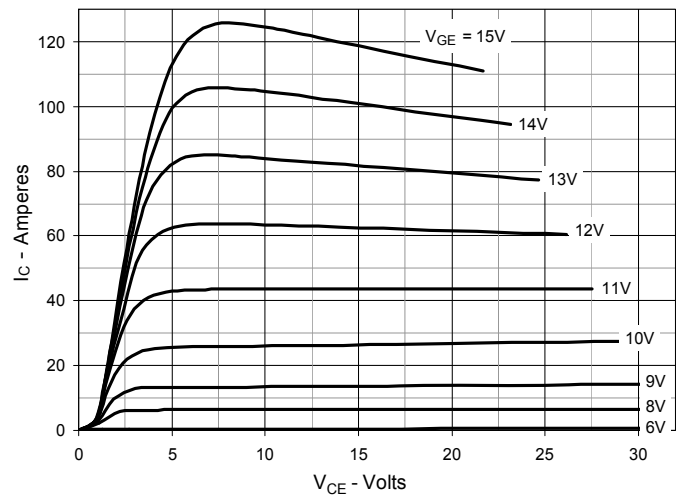
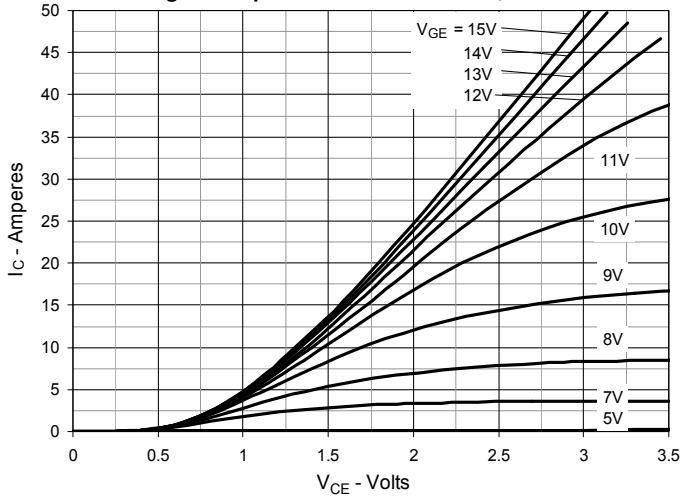
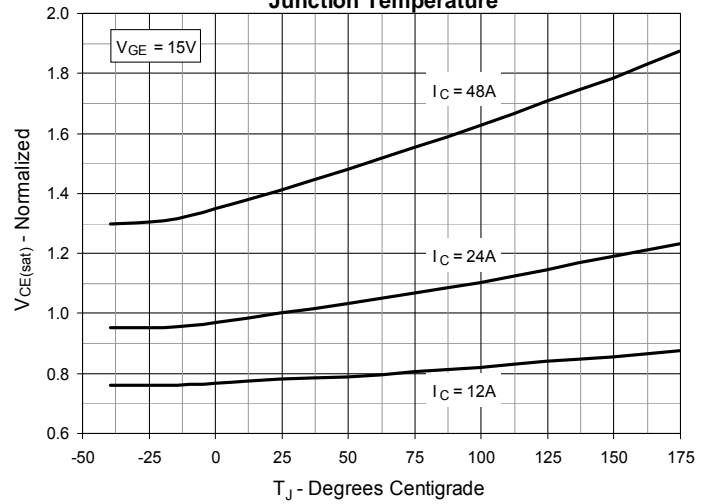
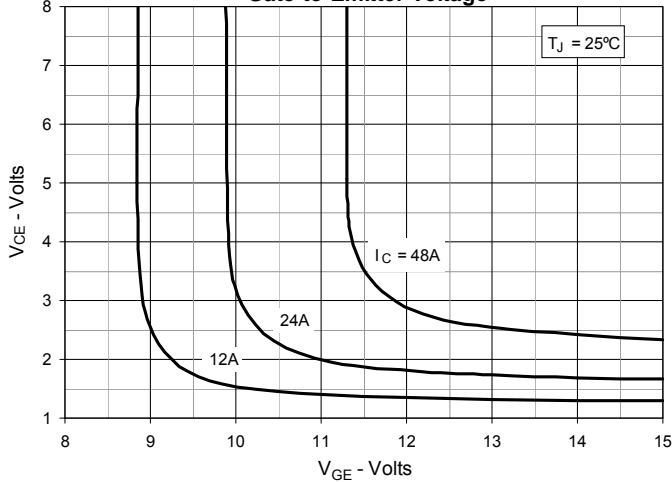
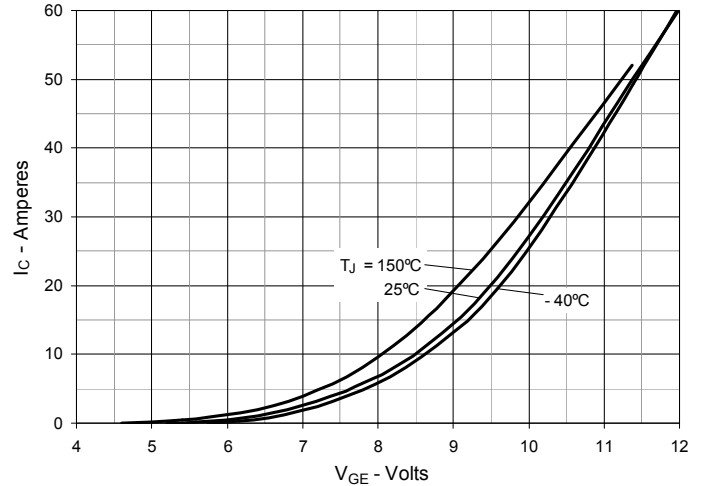
Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

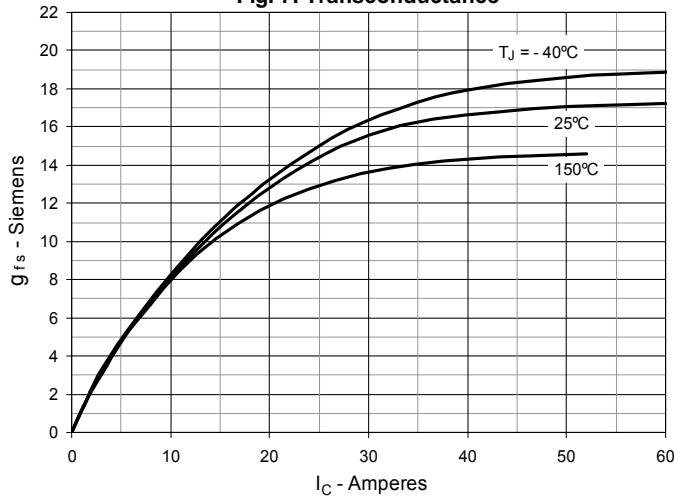
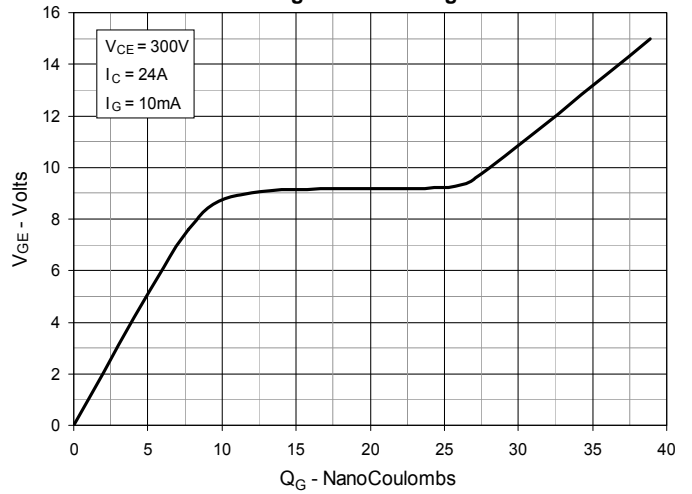
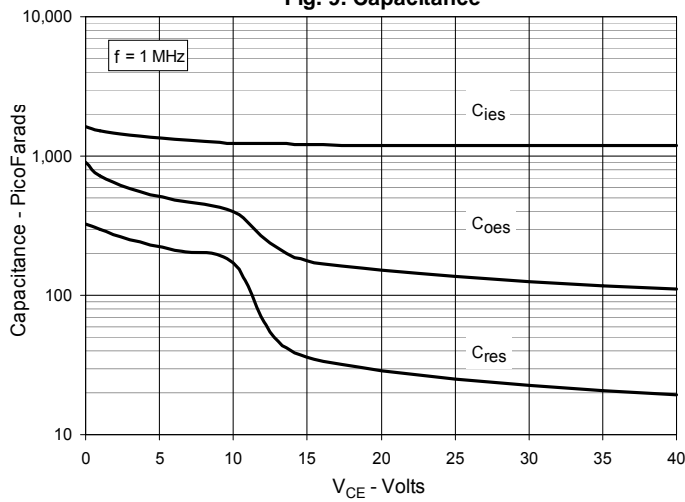
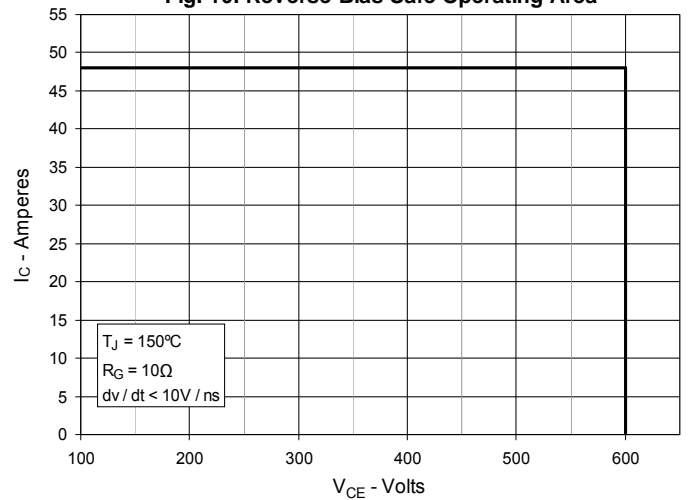
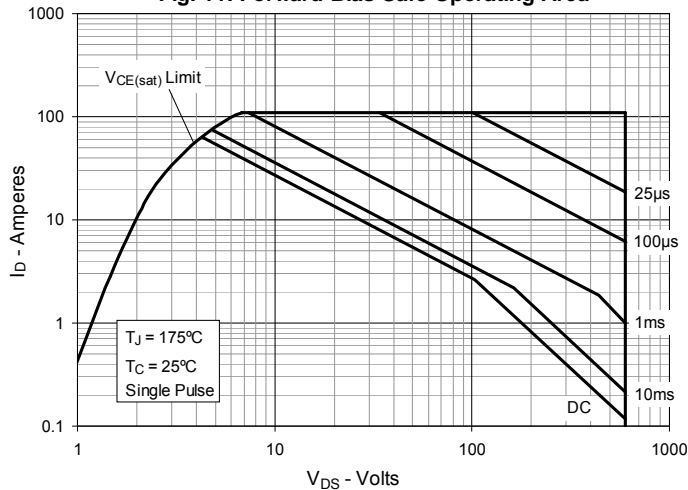
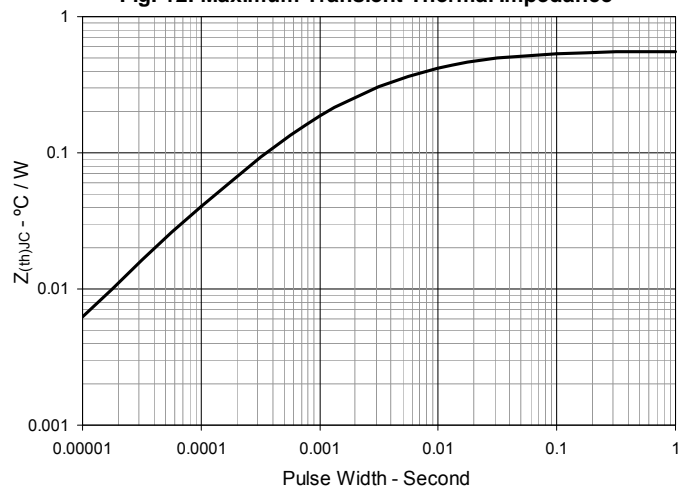
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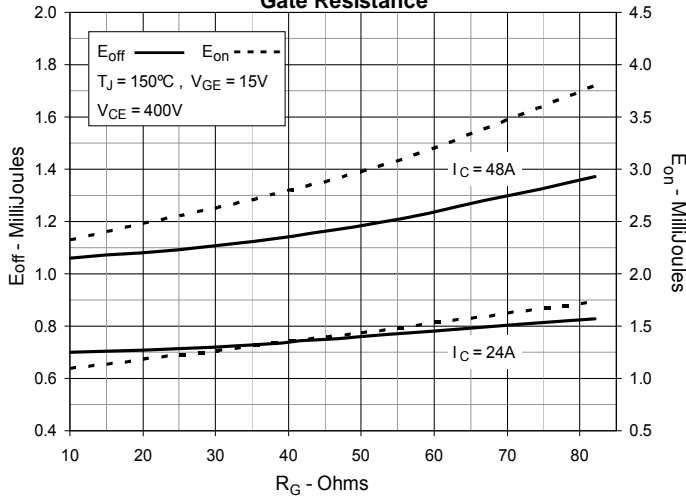
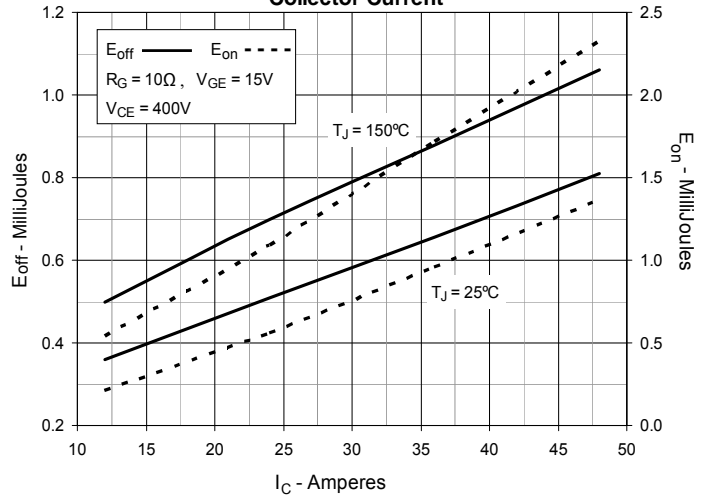
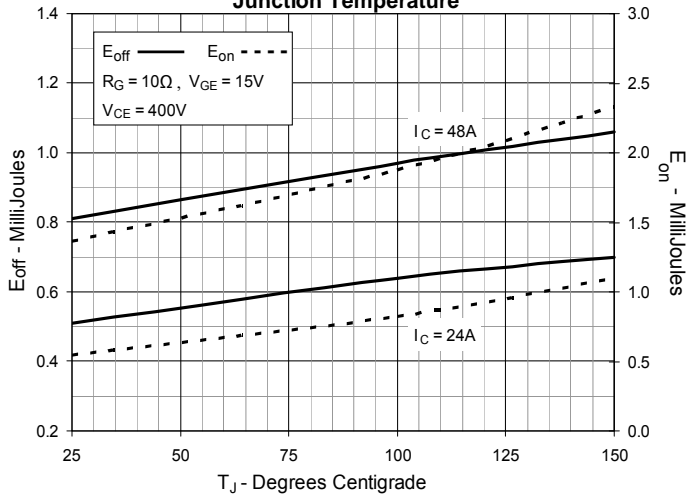
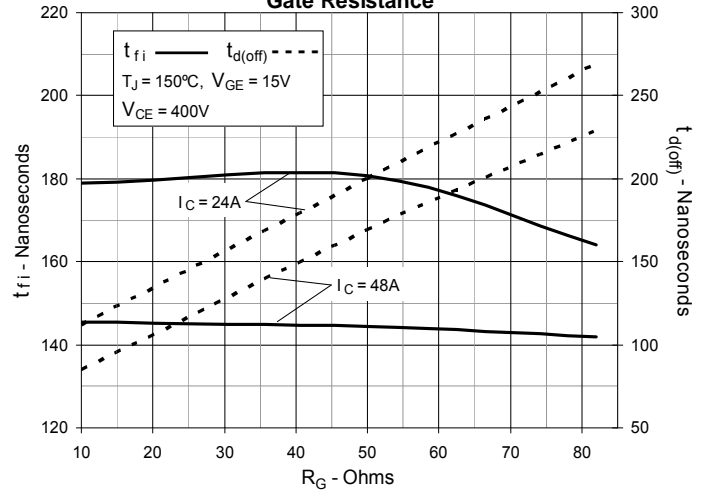
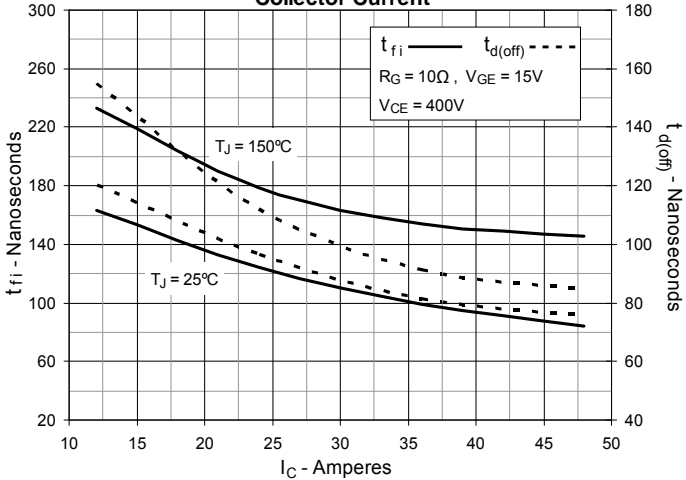
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{clamp})$ ,  $T_J$  or  $R_G$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** 

**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Gate Charge**

**Fig. 9. Capacitance**

**Fig. 10. Reverse-Bias Safe Operating Area**

**Fig. 11. Forward-Bias Safe Operating Area**

**Fig. 12. Maximum Transient Thermal Impedance**


**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**
